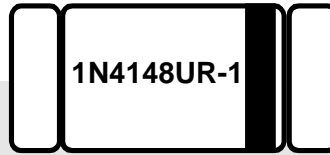


# MINI-MELF-SMD



# Silicon Diode

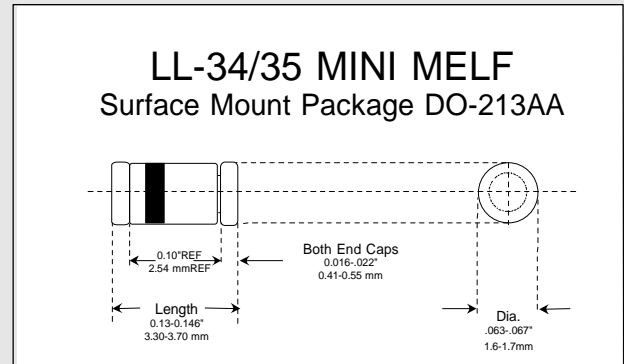
## Applications

Used in general purpose applications, where a low current controlled forward characteristic and fast switching speed are important.

## Switching

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Available in DO-35 package
- Approved to Mil-S-19500/116



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	$I_{Avg}$	200	mAmps
Continuous Forward Current	$I_{Fdc}$	400	mAmps
Peak Surge Current ( $t_{peak} = 1 \text{ sec.}$ )	$I_{peak}$	0.5	Amp
Power Dissipation @ Endcap Temp. = 25 °C	$P_{tot}$	500	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	°C

Electrical Characteristics @ 25 °C*	Symbol	Absolute Limits	Unit
Forward Voltage Drop @ $I_F = 10 \text{ mA}$	$V_F$	1.0	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	$I_R$	0.025	$\mu\text{A}$
Breakdown Voltage @ $I_R = 5 \mu\text{A}$	PIV	75 (MIN)	Volts
Breakdown Voltage @ $I_R = 100\mu\text{A}$	PIV	100 (MIN)	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	$I_R$	0.025 (MAX)	$\mu\text{A}$
Reverse Leakage ( $V_r = 20 \text{ V}, 150 \text{ }^\circ\text{C}$ )	$I_R$	50 (MAX)	$\mu\text{A}$
Capacitance @ $V_R = 0 \text{ V}, f = 1\text{mHz}$	$C_T$	4.0 (MAX)	pF
Reverse Recovery Time (note 1)	$t_{rr}$	4.0 (MAX)	nSecs

Note 1:  $I_F = 10 \text{ mA}, R_L = 100 \text{ Ohms}, V_r = 6.0 \text{ Volts}, I_{rr} = 1.0 \text{ mA}$  \*UNLESS OTHERWISE SPECIFIED



6 Lake Street - Lawrence, MA 01841

Tel: 978-681-0392 - Fax: 978-681-9135